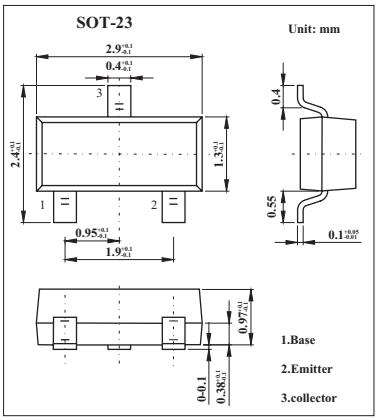
General Purpose Transistors

FMMT4400



Features

- General purpose transistors.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	600	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=0.1mA	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.1mA	6			V
Collector-emitter cut-off current	I_{CEX}	V_{CE}=35V $V_{EB(off)}$ =0.4V			0.1	μA
Base cut-off current	I_{BEX}	V_{CE}=35V $V_{EB(off)}$ =3V			0.1	μA
DC current gain *	h_{FE}	I_C=150mA, V_{CE}=1V	50		150	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=150mA,I_B=15mA I_C=500mA,I_B=50mA			0.4 0.75	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C=150mA,I_B=15mA I_C=500mA,I_B=50mA	0.75		0.95 1.2	V
Current-gain-bandwidth product	f_T	I_C=20mA, V_{CE}=10V f=100KHz	200			MHz
Output capacitance	C_{obo}	V_{CB}=5V, I_E=0, f=100KHz			6.5	pF
Input capacitance	C_{ibo}	V_{BE}=0.5V, I_C=0, f=100KHz			30	pF
Delay time	t_{on}	V_{CC}=30V, I_C=150mA,I_{B1}=15mA $V_{BE(off)}$=2V			35	ns
Storage time	t_{off}	V_{CC}=30V, I_C=150mA I_{B1}= I_{B2}=15mA			255	ns

* Pulse test: tp ⩽ 300 μs; d ⩽ 0.02.

Marking

Marking	1KZ